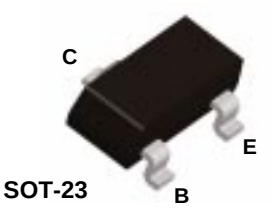
FAIRCHILD SEMICONDUCTOR™

Discrete POWER & Signal Technologies

BCW65C



SOT-23
Mark: ED

NPN General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 500 mA. Sourced from Process 19.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	32	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	1.0	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		***BCW65C**	
P_D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

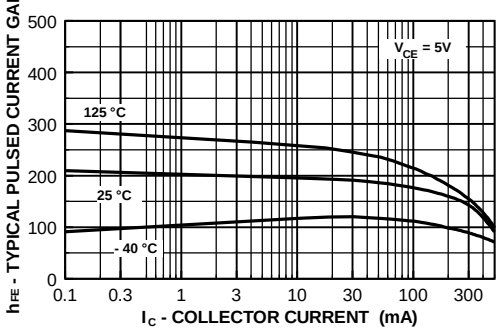
NPN General Purpose Amplifier
(continued)

Electrical Characteristics
TA = 25°C unless otherwise noted

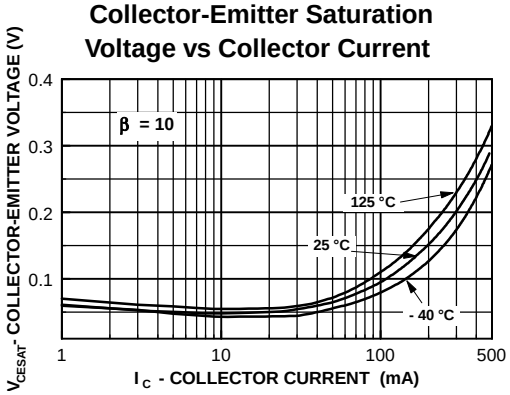
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = 10 mA, I_B = 0	32		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	5.0		V
I_{CES}	Collector-Cutoff Current	V_{CB} = 32 V, I_E = 0 V_{CB} = 32 V, I_E = 0, T_A = 150°C		20 20	nA µA
I_{EBO}	Emitter-Cutoff Current	V_{EB} = 4.0 V, I_C = 0		20	nA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	I_C = 100 µA, V_{CE} = 10 V I_C = 10 mA, V_{CE} = 1.0 V I_C = 100 mA, V_{CE} = 1.0 V I_C = 500 mA, V_{CE} = 2.0 V	80 180 250 50	 630 	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 100 mA, I_B = 10 mA I_C = 500 mA, $_B$ = 50 mA		0.3 0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 500 mA, I_B = 50 mA		2.0	V
SMALL SIGNAL CHARACTERISTICS					
f_T	Current Gain - Bandwidth Product	I_C = 20 mA, V_{CE} = 10 V, f = 100 MHz	100		MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 1.0 MHz		12	pF
C_{ibo}	Input Capacitance	V_{EB} = 0.5 V, I_C = 0, f = 1.0 MHz		80	pF
NF	Noise Figure	I_C = 0.2 mA, V_{CE} = 5.0, R_S = 1.0 kΩ, f = 1.0 kHz, BW = 200 Hz		10	dB

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current

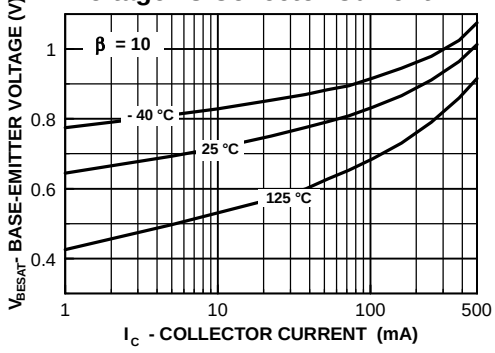


Collector-Emitter Saturation Voltage vs Collector Current

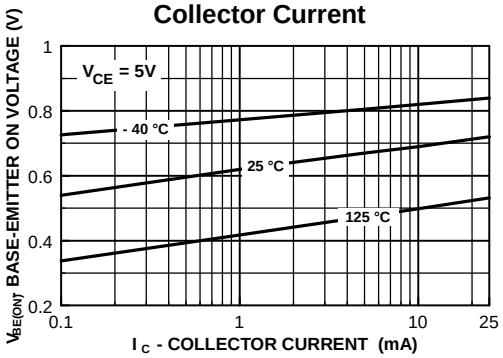


Typical Characteristics

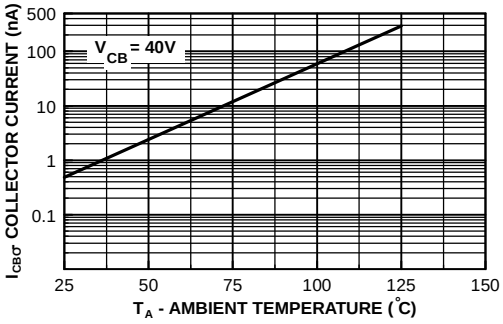
Base-Emitter Saturation Voltage vs Collector Current



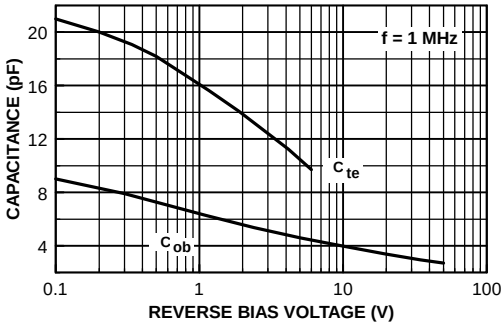
Base-Emitter ON Voltage vs Collector Current



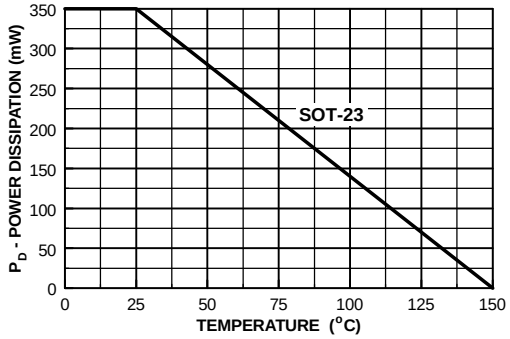
Collector-Cutoff Current vs Ambient Temperature



Emitter Transition and Output Capacitance vs Reverse Bias Voltage



Power Dissipation vs Ambient Temperature



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